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Kind regards,

Team Nexperia



PMBTA44

400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

Rev. 01 — 22 February 2008 Product data s

Product data sheet

Product profile

1.1 General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low current (max. 300 mA)
- High voltage (max. 400 V)
- AEC-Q101 qualified

1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch mode power supply

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|---------------------------|--|-----|-----|-----|------|
| V_{CEO} | collector-emitter voltage | open base | - | - | 400 | V |
| I _C | collector current | | - | - | 300 | mA |
| h _{FE} | DC current gain | $V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA}$ | 50 | - | 200 | |



400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

2. Pinning information

Table 2. Pinning

| Iubic 2. | i iiiiiiig | | |
|----------|-------------|--------------------|--------|
| Pin | Description | Simplified outline | Symbol |
| 1 | base | | |
| 2 | emitter | <u> 3</u> | 3 |
| 3 | collector | 1 2 | 1 — |
| | | | svm021 |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| PMBTA44 | - | plastic surface-mounted package; 3 leads | SOT23 |

4. Marking

Table 4. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| PMBTA44 | W3* |

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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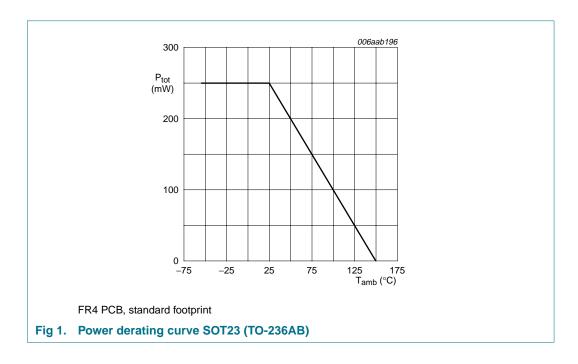
400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

5. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

| | | • • • | • | | |
|------------------|---------------------------|---|--------------|------|------|
| Symbol | Parameter | Conditions | Min | Max | Unit |
| V_{CBO} | collector-base voltage | open emitter | - | 500 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 400 | V |
| V_{EBO} | emitter-base voltage | open collector | - | 6 | V |
| I _C | collector current | | - | 300 | mA |
| I _{CM} | peak collector current | single pulse; $t_p \le 1 \text{ ms}$ | - | 300 | mA |
| I _{BM} | peak base current | single pulse; $t_p \le 1 \text{ ms}$ | - | 100 | mA |
| P _{tot} | total power dissipation | $T_{amb} \le 25 ^{\circ}C$ | <u>[1]</u> _ | 250 | mW |
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | –55 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| | | | | | |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------|---|-------------|--------------|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | <u>[1]</u> _ | - | 500 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

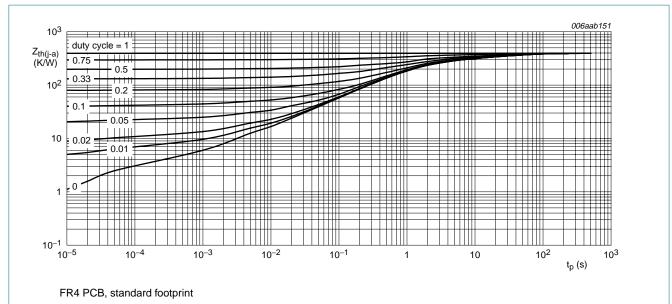


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB)

400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

7. Characteristics

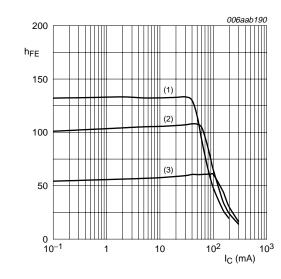
Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

| ann — | | | | | | | |
|--------------------|---|---|------------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| I _{CBO} | collector-base cut-off | $V_{CB} = 320 \text{ V}; I_E = 0 \text{ A}$ | | - | - | 100 | nΑ |
| | current | $V_{CB} = 320 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$ | | - | - | 10 | μΑ |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 4 \text{ V}; I_C = 0 \text{ A}$ | | - | - | 100 | nA |
| h _{FE} | DC current gain | V _{CE} = 10 V | | | | | |
| | | $I_C = 10 \text{ mA}$ | | 50 | - | 200 | |
| | | $I_C = 50 \text{ mA}$ | <u>[1]</u> | 45 | - | - | |
| | | $I_C = 100 \text{ mA}$ | <u>[1]</u> | 40 | - | - | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = 1 \text{ mA}; I_B = 0.1 \text{ mA}$ | | - | - | 400 | mV |
| | | $I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$ | | - | - | 500 | mV |
| | | $I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$ | [1] | - | - | 750 | mV |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$ | <u>[1]</u> | - | - | 850 | mV |
| f _T | transition frequency | $V_{CE} = 10 \text{ V}; I_E = 10 \text{ mA};$ f = 100 MHz | | 20 | - | - | MHz |
| C _c | collector capacitance | $V_{CB} = 20 \text{ V; } I_E = i_e = 0 \text{ A;}$ f = 1 MHz | | - | - | 7 | pF |
| C _e | emitter capacitance | $V_{EB} = 0.5 \text{ V};$ $I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$ | | - | - | 180 | pF |
| | | -6 -6 -7 -7 - 7 - 7 - 7 - 7 - 7 - 7 - 7 | | | | | |

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

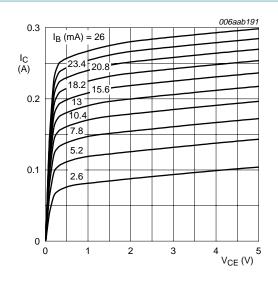
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$$V_{CE} = 10 \text{ V}$$

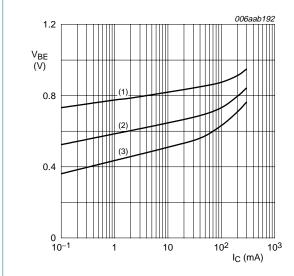
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

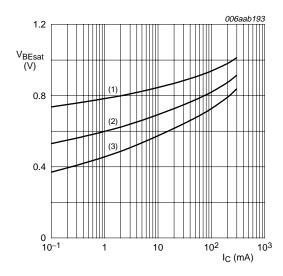
Fig 4. Collector current as a function of collector-emitter voltage; typical values



V_{CE} = 10 V

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

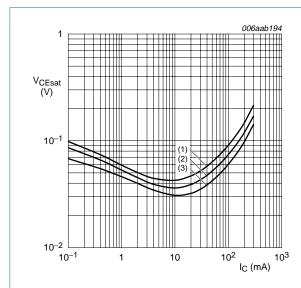


 $I_{\rm C}/I_{\rm B}=5$

- (1) $T_{amb} = -55 \,^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

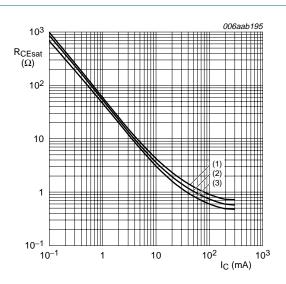
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$$I_{\rm C}/I_{\rm B}=5$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B}=5$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 8. Collector-emitter saturation resistance as a function of collector current; typical values

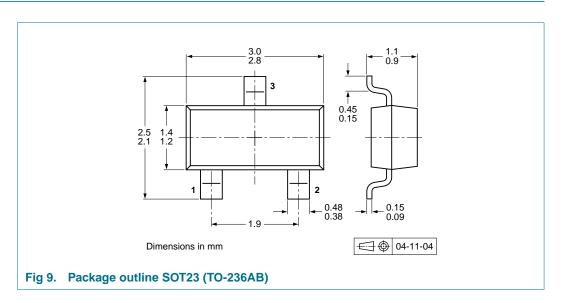
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8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

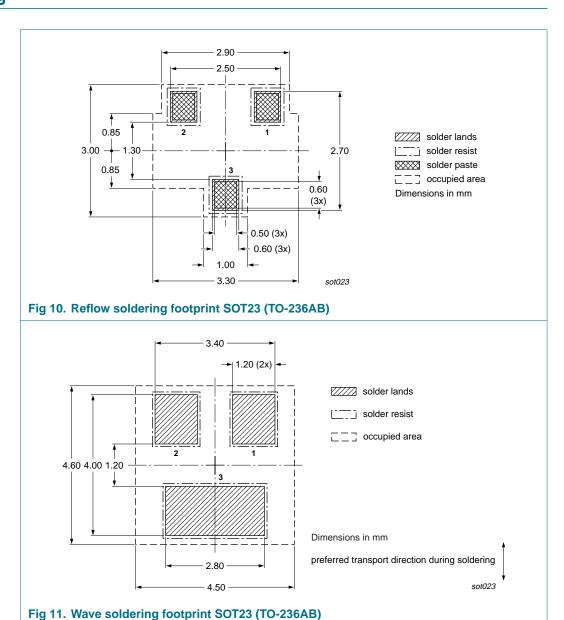
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description | scription Packing quantity | |
|-------------|---------|--------------------------------|----------------------------|-------|
| | | | 3000 | 10000 |
| PMBTA44 | SOT23 | 4 mm pitch, 8 mm tape and reel | -215 | -235 |

^[1] For further information and the availability of packing methods, see $\underline{\text{Section 14}}$.

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11. Soldering



400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

12. Revision history

Table 9. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------|--------------|--------------------|---------------|------------|
| PMBTA44_1 | 20080222 | Product data sheet | - | - |

400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

13. Legal information

13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PMBTA44 **NXP Semiconductors**

400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor

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